

Part III

Reference Material

Appendix A

Frequently Used Symbols

Symbols	Meaning	Units
\mathcal{B}	magnetic induction	Vs/cm ²
c_n, c_p	$c = \nu_{th}\sigma$, electron and hole capture coefficients	cm ³ /s
C_G	gate capacitance	F
C_{ox}	oxide capacitance per unit area	F/cm ²
d_{ox}	oxide thickness	cm
d_s	depletion layer depth	cm
D_n, D_p	diffusion constants of electrons and holes	cm ² /s
\mathcal{E}	electric field	V/cm
E_F	Fermi level	eV
E_F^n, E_F^p	Quasi-Fermi levels of electrons and holes	eV
E_d	defect energy level	eV
E_i	intrinsic energy level	eV
E_C	lower edge of conduction band	eV
E_V	upper edge of valence band	eV
E_G	band gap	eV
\mathcal{E}_s	electric field at semiconductor surface	V/cm
E_t	defect energy level	eV
f	frequency	s ⁻¹
f	fraction of charge induced in the channel	1
\mathcal{F}	force	eV/cm
$F(E)$	Fermi–Dirac occupation probability for electrons	1
$F(E)$	Fermi–Dirac distribution function	1
$F_n(E)$	occupation probability for electrons in the conduction band	1
$F_p(E)$	occupation probability for holes in the valence band	1
F_n	flux density of electrons	cm ⁻² s ⁻¹
F_p	flux density of holes	cm ⁻² s ⁻¹
g	$= \partial I_D / \partial V_D$ transistor conductance	A/V
g_m	$= \partial I_D / \partial V_G$ transistor transconductance	A/V
g_q	$= \partial I_D / \partial Q_{sig}$ DEPFET charge steilheit	s ⁻¹
$g_{m, sat}$	$= \partial I_{D, sat} / \partial V_G$ transconductance in the saturation region	A/V
g_l	defect charge state degeneration factor	1

h	Planck's constant	Js
h	depletion depth	cm
h	potential change in iterative solution of Poisson equation	V
I_D	drain current	A
$I_{D, \text{sat}}$	drain current at saturation	A
J_n, J_p	electron and hole current densities	A/cm ²
G	generation rate	cm ⁻³ s ⁻¹
G_n, G_p	electron and hole generation rates	cm ⁻³ s ⁻¹
k	Boltzmann's constant	J/K, eV/K
k_τ	radiation damage constant (lifetime)	cm ² /s
K_F	1/ f noise parameter	C ² /cm ²
L	transistor channel length	μm
L_n, L_p	diffusion length of electrons and holes	cm, μm
m_n	effective electron mass	kg
m_p	effective hole mass	kg
n	free electron concentration	cm ⁻³
n_i	intrinsic carrier concentration	cm ⁻³
n_n, n_p	electron concentration in n - and p -regions	cm ⁻³
N_A	acceptor concentration	cm ⁻³
N_d	defect concentration	cm ⁻³
N_D	donor concentration	cm ⁻³
N_{eff}	effective doping concentration	cm ⁻³
N_t	defect density	cm ⁻³
N_C	effective density of states in the conduction band	cm ⁻³
N_V	effective density of states in the valence band	cm ⁻³
$N(E_{\text{kin}})$	density of states	1
p	readout pitch	μm
p	free hole concentration	cm ⁻³
p_n, p_p	hole concentration in n - and p -region	cm ⁻³
$P_{t,l}$	probability of defect being in charge state l	1
q	elementary charge	As
Q_c	channel surface charge density	C/cm ²
Q_{inv}	inversion layer surface charge density	C/cm ²
Q_{sig}	signal charge	C
Q_s	space-charge density (in units of e)	cm ⁻³
Q_t	defect charge density (in units of e)	cm ⁻³
R	recombination rate	cm ⁻³ s ⁻¹
R_n, R_p	electron and hole capture rates	cm ⁻³ s ⁻¹
T	absolute temperature	K
U	excess recombination rate	cm ⁻³ s ⁻¹
v_n	noise voltage	V
V_{bi}	built-in voltage	V
V_c	channel potential	V
V_D	drain potential	V
$V_{D, \text{sat}}$	drain-source saturation voltage	V

V_F	flat-band voltage	V
V_G	gate potential	V
$V_{G, \text{eff}}$	effective gate voltage	V
V_p	pinch-off voltage	V
V_{sub}	substrate potential	V
V_S	source potential	V
V_T	threshold voltage	V
V_T	$= \frac{kT}{q}$ thermal voltage	V
W	transistor channel width	μm
$x(E)$	$= \exp(\frac{E - E_i}{kT})$	1
α	radiation-damage constant (current)	A/cm
α_l	ratio of probabilities of neighboring defect charge states	1
α_T	transistor base-transport factor	1
α_0	transistor common-base current gain	1
β	generation constant	$\text{cm}^{-3}\text{s}^{-1}$
β	transistor current gain	1
γ	transistor emitter efficiency	1
ϵ	dielectric constant	1
ϵ_0	permittivity in a vacuum	F/cm
Θ_n, Θ_p	Hall angle of electrons and holes	1
μ_n, μ_p	mobility of electrons and holes	cm^2/Vs
μ_n^H, μ_p^H	Hall mobility of electrons and holes	cm^2/Vs
ν_n, ν_p	drift velocity of electrons and holes	cm/s
$\nu_{\text{th},n}, \nu_{\text{th},p}$	thermal velocity of electrons and holes	cm/s
ρ	charge density	C/cm^3
σ	root-mean-square deviation	μm
σ_n, σ_p	electron and hole capture cross-sections	cm^2
τ_c	mean free time between collisions	s
τ_r	recombination life-time of minority carriers	s
τ_g	generation life-time of minority carriers	s
Φ	potential	V
Φ	radiation fluence	cm^{-2}
$q\Phi_m$	work function of metal	eV
$q\Phi_s$	work function of semiconductor	eV
$q\Phi_{B_n}, q\Phi_{B_p}$	barrier height of metal-semiconductor contact	eV
Ψ_B	$\frac{1}{q} E_i - E_F $, distance intrinsic level to Fermi level	V
Ψ_c	channel potential	V
Ψ_s	potential at the semiconductor surface	V
$q\chi$	electron affinity	eV

Appendix B

Physical Constants

Quantity	Symbol	Value (in one or two units)
Ångström unit Electron volt	Å eV	$1 \text{ Å} = 10^{-8} \text{ cm} = 10^{-10} \text{ m}$ $1.6022 \times 10^{-19} \text{ J}$
Speed of light Permittivity of free space Permeability of free space	c ϵ_0 μ_0	$2.99792 \times 10^{10} \text{ cm/s}$ $8.85418 \times 10^{-14} \text{ F/cm}$ $1.25663 \times 10^{-8} \text{ H/cm}$
Planck's constant Reduced Planck constant	h \hbar	$6.62617 \times 10^{-34} \text{ J s}$ $1.05458 \times 10^{-34} \text{ J s}$
Elementary charge Electron rest mass Proton rest mass	q m M_p	$1.60218 \times 10^{-19} \text{ C}$ $0.91095 \times 10^{-27} \text{ g}$ $1.67264 \times 10^{-27} \text{ kg}$
Ideal gas constant	R	$1.98719 \text{ cal/mole K}$ $= 8.3145 \text{ J/mole K}$
Boltzmann's constant Avogadro's number	$k = R/N_A$ N_A	$1.3087 \times 10^{-23} \text{ J/K}$ $6.0221 \times 10^{23} \text{ mole}^{-1}$
Thermal voltage at 300 K	$V_T = kT/q$	0.0259 V
Wavelength of 1-eV quantum	λ	$1.23977 \text{ }\mu\text{m}$

References

Books and Reviews

- Beadle, W.E., Tsai, J.C.C. and Plummer, R.D. (1984): "Quick Reference Manual for Silicon Integrated Circuit Technology" John Wiley and Sons, New York, Chichester, Brisbane, Toronto, Singapore, 1984
- Gatti, E. and Manfredi, P.F. (1986): "Processing the signals from solid state detectors in elementary particle physics" *Rivista di Nuovo Cimento* 9, Ser. 3 (1986) 1-145
- Gray, P.R. and Meyer, R.G. (1993): "Analysis and design of analog integrated circuits" 3rd ed., Wiley, New York 1993
- Grove, A.S. (1967): "Physics and technology of semiconductor devices" Wiley, New York 1967
- Henke, B.L. (1982) et al.: *Atomic Data Tables*, Vol. 27 (1982) 1
- Kittel, C. (1976): "Introduction to solid state physics" Wiley, New York 1976
- Knoll, Glenn F. (1989): "Radiation detection and measurement" 2nd ed., Wiley and Sons, New York 1989
- Landolt-Börnstein vol. III/17a (1982): "Semiconductors, Physics of Group IV Elements and III-V Compounds" Springer, Berlin Heidelberg New York, 1982
- Landolt-Börnstein vol. III/17c (1984): "Semiconductors, Technology of Si, Ge and SiC" Springer, Berlin Heidelberg New York, 1984
- Landolt-Börnstein vol. III/22a (1987): "Semiconductors, Intrinsic Properties of Group IV Elements and III-V, II-VI and I-VII Compounds" Springer, Berlin Heidelberg New York, 1987
- Leo, W.R. (1994): "Techniques for Nuclear and Particle Physics Experiments" Springer, Berlin Heidelberg New York
- Muller-Kamins (1986): "Device electronics for integrated circuits" 2nd ed., John Wiley & Sons, New York
- Nicollian, E.H. and J.R. Brews (1982): "MOS Physics and Technology" John Wiley & Sons, New York
- Palik, E.D. (1985): "Handbook of optical constants of solids" Academic Press, New York
- Shockley, W. (1950): "Electrons and holes in semiconductors" D. van Nostrand Company Inc., New York
- Smith, R.A. (1979): "Semiconductors" 2nd ed., Cambridge University Press, London 1979
- Spenke, E. (1965): "Elektronische Halbleiter" 2nd ed., Springer Verlag, Berlin, Heidelberg, New York 1965

- Sze, S.M. (1981): "Physics of semiconductor devices" 2nd ed. Wiley, New York 1981
- Sze, S.M. (1983): "VLSI Technology" McGraw-Hill, New York 1983
- Sze, S.M. (1985): "Semiconductor devices, physics and technology" Wiley, New York 1985
- Sze, S.M. (1994): "Semiconductor sensors" Wiley, New York 1994
- Van Lint, V.A.J., Flanagan, T.M., Leadon, R.E., Naber, J.A., and Rogers, V.C. (1980): "Mechanisms of radiation effects in electronic materials, volume 1" John Wiley and Sons, 1980
- Veigele, W.J. (1973): Atomic Data Tables, Vol. 5 No.1 (1973) 51
- Wang, S. (1989): "Fundamentals of Semiconductor Theory and Device Physics" Prentice Hall, Englewood Cliffs, New Jersey

Articles

- Abe, K., Arodzero, A. (1997) et al.: "Design and performance of the SLD vertex detector: a 307 Mpixel tracking system" Nucl. Instr. and Meth. A400 (1997) 287-343
- Alig, R.C., Bloom, S. and Struck, C.W. (1980): "Scattering by ionization and phonon emission in semiconductors" Phys. Rev. B, Vol 22, no.12 (1980) 5565-5582; "Scattering by ionization and phonon emission in semiconductors II. Monte Carlo calculations" Phys. Rev. B, Vol 27, no. 2 (1983) 968-977
- Anghinolfi, F., Dabrowski, W. (1997) et al.: "SCTA - a rad-hard BiCMOS analogue readout ASIC for the ATLAS semiconductor tracker" IEEE Trans. Nucl. Sci. 44 (1997) 298-302
- Bailey, R., Damerell, C.J.S. (1983) et al.: "First Measurements of Efficiency and Precision of CCD Detectors for High Energy Physics" Nucl. Instr. and Meth. 213 (1983) 201-215
- Bak, J.F., Burenkov, A. (1987) et al.: "Large departures from Landau distributions for high-energy particles traversing thin Si and Ge targets" Nucl. Phys. B288 (1987) 681-716
- Belau, E., Klanner, R. (1983a) et al.: "Charge collection in silicon strip detectors" Nucl. Instr. and Meth. 214 (1983) 253-260
- Belau, E., Kemmer, J. (1983b) et al.: "Silicon detectors with 5 μm spatial resolution for high energy particles" Nucl. Instr. and Meth. 217 (1983) 224-228
- Bethe, H.A. (1930): "Zur Theorie des Durchgangs schneller Korpuskularstrahlen durch Materie" Ann. d. Phys. 5 (1930) 325
- Beutenmüller, R.H., Kraner, H.W. (1987) et al.: "Silicon position sensitive detectors for the Helios (NA34) experiment" Nucl. Instr. and Meth. A253 (1987) 500-510
- Beuville, E., Borer, K. (1990) et al.: "AMPLEX, a low-noise low-power analog CMOS signal processor for multielement silicon particle detectors" Nucl. Instr. and Meth. A288 (1990) 157-167
- Bichsel, H. (1988): "Straggling in thin Silicon detectors" Rev. Mod. Phys. 60 (1988) 663-699

- Bloch, F. (1933): "Bremsvermögen von Atomen mit mehreren Elektronen" *Z. Phys.* 81 (1933) 363
- Buskalic, D., Casper, D. (1995) et al.: "Performance of the ALEPH detector at LEP" *Nucl. Instr. and Meth.* A360 (1995) 481-506
- Buttler, W., Lutz, G. (1988) et al.: "Low-noise, low power monolithic multiplexing readout electronics for silicon strip detectors" *Nucl. Instr. and Meth.* A273 (1988) 778-783
- Caccia, M., Evensen, L. (1987) et al.: "A Si Strip Detector with Integrated Coupling Capacitors" *Nucl. Instr. & Meth.* A260 (1987) 124-131
- Castoldi, A., Rehak, P. (1996) et al.: "A new drift detector with reduced lateral diffusion" *Nucl. Instr. and Meth.* A377 (1996) 375-380
- Cesura, G., Findeis, N. (1996) et al.: "New pixel detector concepts based on junction field effect transistors on high resistivity silicon" *Nucl. Instr. and Meth.* A377, 521-528 (1996)
- Chen, W., Kraner, H. (1992) et al.: "Large area cylindrical silicon drift detector" *IEEE Trans.Nucl.Sci.* 39 (1992) 619-628
- Cottini, C., Gatti, E., Gianelli, G. and Rozzi, G. (1956): "Minimum noise preamplifiers for fast ionization chamber" *Nuovo Cimento* (1956) 473-483;
- Damerell, C.J.S., English, R.L. (1987) et al.: "CCDs for Vertex Detection in High Energy Physics" *Nucl. Instr. and Meth.* A253 (1987) 478-481;
- Damerell, C.J.S., English, R.L. (1990) et al.: "A CCD based vertex detector for SLD" *Nucl. Instrum. Methods* A288 (1990) 236-239
- Decamp, D., Deschizeaux, B. (1990) et al.: "A detector for electron-positron annihilations at LEP" *Nucl. Instrum. Methods* A294 (1990) 121-178
- Dentan, M., Abbon, P. (1996) et al.: "DMILL, a mixed analog-digital radiation-hard BICMOS technology for High Energy Physics electronics" *IEEE Trans. Nucl. Sci.* 43 (1996) 1763-1767
- Di Maria, D.J., Arnold, D. and Cartier, E. (1993): "Impact ionization and degradation in silicon dioxide films on silicon", in: C.R. Helms and B.E. Deal (eds.), *The Physics and Chemistry of SiO₂ and the Si-SiO₂ Interface 2* (Plenum Press, New York, 1993)
- Fano, U. (1947): "Ionization yield of radiations II: The fluctuations of the number of ions" *Phys. Rev.* 72 (1947) 26-29
- Farell, R., Vanderpuye, K. (1994) et al.: "Radiation detection performance of very high gain avalanche photodiodes" *Nucl. Instr. and Meth.* A353(1994) 176-179
- Feick, H., Fretwurst, E. (1996) et al.: "Long term damage studies using silicon detectors fabricated from different starting materials and irradiated with neutrons, protons and pions" *Nucl. Instr. and Meth.* A377 (1996) 217-223
- Fraser, G.W., Abbey, A.F. (1974) et al.: "The X-ray energy response of silicon" *Nucl. Instr. and Meth.* A350 (1994) 368-378
- Fretwurst, E., Herdan, H. (1990) et al.: "Silicon detector developments for calorimetry: technology and radiation damage" *Nucl. Instr. & Meth.* A288, (1990) 1-12
- Fretwurst, E., Feick, H. (1994) et al.: "Reverse annealing of the effective impurity concentration and long term operational scenario for silicon detectors

- detectors in future collider experiments" Nucl. Instr. & Meth. A342, (1994) 119-125
- Gadomski, S., Hall, G. (1992) et al.: "The deconvolution method of fast pulse shaping at hadron colliders" Nucl. Instr. & Meth. A320, (1992) 217-227
- Gajewski, H., Heinemann, B., Langmach, H., Telschow, G., and Zacharias, K. (1992): "TOSCA - Two dimensional Semiconductor Analysis Package", Handbuch, Karl-Weierstraß Institut, Berlin 1992
- Gatti, E. and Rehak, P. (1984a): "Semiconductor Drift Chamber - An Application of a Novel Charge Transport Scheme" Nucl. Instr. and Meth. 225 (1984) 608-614;
- Gatti, E., Rehak, P. (1984b) et al.: "Silicon Drift Chambers - First results and optimum processing of signals" Nucl. Instr. and Meth. 226 (1984) 129-141;
- Gatti, E., Rehak, P. (1985) et al.: "Semiconductor Drift Chambers" IEEE Trans.Nucl.Sci. 32 (1985) 1204-1208;
- Hall, R.N. (1952): "Electron-hole recombination in germanium" Phys. Rev. 87 (1952) 387
- Hartmann, R., Strüder, L. (1997) et al.: "Ultrathin entrance windows for silicon drift detectors" Nucl. Instr. and Meth. A387 (1997) 250-254
- Heijne, E.H.M., Hubbeling, L. (1980) et al.: "A silicon surface barrier microstrip detector designed for high energy physics" Nucl. Instr. and Meth. 178 (1980) 331-341
- Heijne, E.H.M., Antinori, F. (1994) et al.: "First operation of a 72 k element hybrid silicon micropattern pixel detector array" Nucl. Instr. and Meth. A349 (1994) 138-155
- Heijne, E.H.M., Antinori, F. (1996) et al.: "LHC1: a semiconductor pixel detector readout chip with internal, tunable delay providing a binary pattern of selected events" Nucl. Instr. and Meth. A383 (1996) 55-63
- Hofmann R., Lutz, G. (1984) et al.: "Development of readout electronics for monolithic integration with diode strip detectors" Nucl. Instr. and Meth. 226 (1984) 196-199
- Kandiah, K., Deighton, M.O. and Whiting, F.B. (1981): "Low frequency noise mechanisms in field effect transistors" Proc. 6th Conf. on noise in physical systems, NBS Publication 614, U.S. Department of Commerce, 1981
- Kandiah, K. (1983): "Energy levels of bulk defects responsible for L.F. noise in Si JFETs" Noise in Physical Systems and $1/f$ Noise, pg 287-290, Elsevier Science Publishers B.V., 1983
- Kandiah, K. (1986): "Low frequency noise mechanisms in field effect transistors" Noise in Physical Systems and $1/f$ Noise, pg 19-25, Elsevier Science Publishers B.V., 1986
- Kandiah, K., Deighton, M.O. (1989) et al.: "A physical model for random telegraph signal currents in semiconductor devices" J. Appl. Phys. 66, (1989) 937-948
- Kemmer, J. (1980): "Fabrication of low noise silicon radiation detectors by the planar process" Nucl. Instr. & Meth. A169 (1980) 499-502
- Kemmer, J. and Lutz, G. (1987): "New semiconductor detector concepts" Nucl. Instr. & Meth. A253 (1987) 356-377

- Kemmer, J., Lutz, G. (1987) et al.: "Low capacitive drift diode" Nucl. Instr. & Meth. A253 (1987) 378-381
- Kemmer, J. and Lutz, G. (1988): "New structures for position sensitive semiconductor detectors" Nucl. Instr. & Meth. A273 (1988) 588-598
- Kemmer, J., Lutz, G. (1990) et al.: "Experimental confirmation of a new semiconductor detector principle" Nucl. Instr. & Meth. A288 (1990) 92-98
- Kemmer J. and Lutz, G. (1993): "Concepts for simplification of strip detector design and production" Nucl. Instr. and Meth. A326 (1993) 209-213
- Kleinfelder, S.A., Carithers, W.C. jr. (1988) et al.: "A flexible 128 channel silicon strip detector instrumentation integrated circuit with sparse readout" IEEE Trans. Nucl. Sci. 35 (1988) 171-175
- Landau, L. (1944): J. Phys. (USSR) 8 (1944) 201
- Lechner, P., Hartmann, R., Soltau, H. and Strüder, L. (1996): "Pair creation energy and Fano factor of silicon in the energy range of soft x-rays" Nucl. Instr. and Meth. A377 (1996) 206-208
- Li, Z. (1994): "Modelling and simulation of neutron induced changes and temperature annealing of N_{eff} and changes in resistivity in high resistivity silicon detectors" Nucl. Instr. and Meth. A342 (1994) 105-118
- Longoni, A., Gatti, E. and Sacco, R. (1995): "Trapping noise in semiconductor devices: a method for determining the noise spectrum as a function of the trap position" Journal of Applied Physics 78 (1995) 6283-6297
- Longoni, A. (1990), Sampietro, M. and Strüder, L.: "Instability of the breakdown of high resistivity silicon detectors due to the presence of oxide charges" Nucl. Instr. and Meth. A288 (1990) 35-43
- Lumb, D. (1997) et al: "X-ray Multi-Mirror Mission – an overview" SPIE 2808 (1997) 326
- Lutz, G. (1986): "Present and Future Semiconductor Tracking Detectors" Vertex Detectors, Plenum Press, New York, 1988, pp. 195-224
- Lutz, G. (1991): "Correlated noise in silicon strip detector readout" Nucl. Instr. and Meth. A309 (1991) 545-551
- Lutz, G. (1994): "A simplistic model for reverse annealing in irradiated silicon" Nucl. Instr. and Meth. B95 (1995) 41-49
- Lutz, G. (1996): "Effects of deep level defects in semiconductor detectors" Nucl. Instr. and Meth. A377 (1996) 234-243
- Matheson, J. (1996), M. Robbins and S. Watts: "The effect of radiation induced defects on the performance of high resistivity silicon diodes", Nucl. Instr. and Meth. A377 (1996) 224-227
- Mours, B., Boudreau, J. (1996) et al.: "The design, construction and performance of the ALEPH silicon vertex detector" Nucl. Instr. and Meth. A379 (1996) 101-115
- Nyquist, H. (1928): "Thermal agitation of electrical charge in conductors" Phys. Rev. 32 (1928) 110-113
- Parker, S.I., Kenney, C.J. (1994) et al.: "A prototype monolithic pixel detector"
- Pinotti, E., Bräuninger, H. (1993) et al: "The pn-CCD on-chip electronics" Nucl. Instr. and Meth. A326 (1993) 85-91

- Pitzl, D., Cartiglia, N. (1992) et al.: "Type inversion in silicon detectors" Nucl. Instr. and Meth. A311 (1992) 98-104
- Radeka, V., Rehak, P. (1989) et al.: "Implanted silicon JFET on completely depleted high resistivity devices" IEEE Electron device letters 10 (1989) 91-95
- Rehak, P., Gatti, E. (1985) et al.: "Semiconductor drift chambers for position and energy measurements" Nucl. Instr. & Meth. A235 (1985) 224-234
- Rehak, P., Walton, J. (1986) et al.: "Progress in semiconductor drift detectors" Nucl. Instr. & Meth. A248 (1986) 367-378
- Rehak, P., Gatti, E. (1989) et al.: "Spiral silicon drift detectors" IEE Trans. Nucl. Sci. 36 (1989) 203-209
- Rehak, P., Rescia, S. (1990) et al.: "Feedback charge amplifier integrated on detector wafer" Nucl. Instr. and Meth. A288 (1990) 168-175
- Richter, G. (1996) et al.: "ABRIXAS, A Broadband Imaging X-ray All-sky Survey"; L. Bassani, G.di Cocco (eds.): Imaging in High Energy Astronomy. Experm. Astron., (1996) 159
- Richter, R.H., Andricek, L. (1996) et al.: "Strip detector design for ATLAS and HERA-B using two dimensional device simulation" Nucl. Instr. and Meth. A377 (1996) 412-421
- Sansen, W. (1987): "Integrated low noise amplifiers in CMOS technology" Nucl. Instr. and Meth. A253 (1987) 427-433
- Scharfetter, D.L. and Gummel, H.K. (1969): "Large-signal analysis of a silicon Read diode oscillator", IEEE Trans. ED-16 (1969) 64-77
- Shapiro, S.L., Dunwoodie, W.M. (1989) et al.: "Silicon PIN diode array hybrids for charged particle detection" Nucl. Instr. and Meth. A275 (1989) 580-586
- Sedlmeir, J. (1985): "Untersuchung über einseitig und zweiseitig auslesbare Siliziumstreifendetektoren" Diplomarbeit, Technische Universität München, 15. August 1985
- Shockley, W. and Read, W.T. (1952): "Statistics of the recombination of holes and electrons" Phys. Rev. 87 (1952) 835-842
- Soltau, H., Holl, P. (1996) et al.: "Performance of the pn-CCD detector system designed for the XMM satellite mission" Nucl. Instr. and Meth. A377 (1996) 340-345
- Strüder, L., Bräuninger, H. (1990) et al.: "The MPI/AIT x-ray imager (MAXI) - high speed pn-CCDs for x-ray detection" Nucl. Instr. and Meth. A288 (1990) 227-235
- Strüder, L., Bräuninger, H. (1993) et al.: "First results with the pn-CCD detector system for the XMM satellite mission" Nucl. Instr. and Meth. A326 (1993) 129-135
- Strüder, L., Bräuninger, H. (1997) et al.: "A 36 cm² large monolithic pn-charge coupled device x-ray detector for the European XMM satellite mission" Rev.Sci.Instrum. 68 (1997) 4271-4274
- Tapan, I., Duell, A.R. (1997) et al.: "Avalanche photodiodes as proportional particle detectors" Nucl. Instr. and Meth. A388 (1997) 79-90

- Toker, O., Masciocchi, S. (1994) et al.: "VIKING, a CMOS low noise monolithic 128 channel frontend for Si-strip detector readout" Nucl. Instr. and Meth. A340 (1994) 572-579
- Vasilescu, A. (1998) et al.: "Fluence normalisation based on the NIEL scaling hypothesis", 3rd ROSE Workshop, DESY Hamburg, 12-14 February 1998, DESY-Proc. 1998-2
- Walker, J.T., Parker, S. (1984) et al.: "Development of high density readout for silicon strip detectors" Nucl. Instr. and Meth. 226 (1984) 200-203
- Wunstorf, R. (1992a): "Systematische Untersuchungen zur Strahlenresistenz von Silizium-Detektoren für die Verwendung in Hochenergiephysik-Experimenten" Ph.D. thesis, Universität Hamburg, 1992
- Wunstorf, R., Benkert, M. (1992b) et al.: "Results on radiation hardness of silicon detectors up to neutron fluences of 10^{15} n/cm²" Nucl. Instr. and Meth. A315 (1992) 149-155

Index

- Abrupt change approximation, 41, 62, 69, 175
- Absorption length (of photons), 92, 99
- Acceptor, 15
- Acceptor removal, 289
- Accumulation, 60, 64, 69
- Accumulation layer, 64, 65, 121, 122
- A-center, 276, 278
- Activation, 84, 264
- Activation energy, 297
- Active load, 198
- Annealing, 265, 297, 298
- Avalanche breakdown, 27, 51, 54
- Avalanche diode, 26, 239, 240, 242

- Band gap, 12
- Barrier height, 56, 58
- Base transport factor, 155, 156, 158, 308
- Bernoulli function, 325
- Bethe, 23
- Bethe–Bloch formula, 23, 24
- Biasing
 - field effect transistor, 218
 - punch through, 122, 123, 135, 221
 - resistive, 218
- BICMOS technology, 207
- Bipolar technology, 203, 206
- Bloch, 23
- Bohr, 23
- Bond representation, 9
- Breakdown, 107, 159, 267, 273, 305
- Built-in voltage, 40, 42
- Buried layer, 262

- Capacitance voltage characteristics
 - of a diode, 49
 - of the MOS structure, 69, 70
- Capture cross-section, 184, 186

- Carrier lifetime, 70
- Carrier transit time, 177
- Cascode amplifier, 201
- Cascode circuit, 196
- Channel conductance
 - of a JFET, 162
- Charge–carrier lifetime, 29
- Charge collection, 93, 102, 114, 141, 148
- Charge coupled device (CCD), 137–151
 - buried-channel CCD, 138, 142–144
 - linear CCD, 140
 - matrix CCD, 140
 - MOS CCD, 138–140, 144
 - p - n CCD, 137, 138, 144–151
 - readout, 143
 - two phase CCD, 144
- Charge division, 109, 112, 113, 225
 - capacitive, 112, 113, 211, 212
 - readout, 225
 - resistive, 109, 112
- Charge multiplication, 26, 54, 240, 242
- Charge-sensitive amplifier (CSA), 190, 192–194, 199, 217
- Charge-transfer loss, 136
- Chemical vapour deposition (CVD), 93
- CMOS technology, 197, 203, 205, 309
- Collector–base current gain, 158
- Common base current gain, 156, 158
- Common emitter configuration, 158
- Compton effect, 91
- Conduction band, 10
- Conductor, 10
- Contact illumination, 261
- Continuity equation, 35, 44, 314, 320, 324

- Corner frequency, 189, 192
- Crystal defect, 83, 84, 142, 184
- Current mirror, 196, 197
- Current source, 196
- Current–voltage characteristics
 - of a diode, 49
 - of a JFET, 162
 - of a metal–semiconductor contact, 58
 - of a *p*-channel MOSFET, 170
 - of an *n*-channel MOSFET, 166
- Czochralski, 260

- Damage constant, 292
- Deconvolution method, 209
- Defect cluster, 87, 275–277
- Defect complex, 87, 277–279, 288, 289, 297, 298
- Defect level, 32, 320
- Defect occupation probability, 32, 33
- Degeneration factor, 286, 287
- Density of states, 11, 12
- DEPFET (Depleted Field Effect Transistor), 234, 243, 244, 247, 251–253
- DEPJFET, 252
- Depletion, 60, 66, 69
- Depletion depth, 67
- Depletion layer, 66
- DEPMOS (Depleted MOS Transistor), 247
- Diamond lattice, 7, 8
- Differential amplifier, 202
- Diffusion, 16, 17, 262
- Diffusion constant, 18
- Diffusion current, 43, 44, 95, 157
- Diffusion equation, 17, 97
- Diffusion length, 45, 47, 96, 97, 141, 157
- Diffusion voltage, 40
- Diode, 39–55, 100
- Direct semiconductors, 11, 28
- Displacement energy, 276
- Divacancy, 276, 278, 286, 288
- DLTS (Deep Level Transient Spectroscopy), 297
- Donor, 15
- Donor removal, 278, 289, 301
- Dopant, 84, 85, 262
- Doping, 14, 84, 262
 - density, 70
- Double-correlated sampling, 194, 195
- Drift, 16, 17
- Drift detector, 125–137
 - linear, 127
 - matrix, 132
 - radial, 133
 - single-sided structured, 134, 135, 237, 238
- Drift mobility, 20
- Drift velocity, 17
- Dry ion etching, 262
- Dynamic range, 147

- E-center, 87, 276, 278
- Effective density of states, 12
- Effective doping, 289, 290, 298
- Effective mass, 10, 12
- Einstein equation, 18, 19, 324
- Electron affinity, 56
- Electron capture, 32, 279, 281, 287
 - cross-section, 286
- Electron emission, 32, 279, 281
- Emitter efficiency, 155, 158
- Energy band, 9
- Energy loss, 109
 - rate, 23
- Epitaxial growth, 263, 264
 - techniques, 207, 242
- Evaporation, 264
- Excess generation, 321
 - rate, 44, 315
- Excess recombination, 44
- Extrinsic semiconductors, 12, 14

- Fano factor, 91, 92, 148
- Fermi–Dirac function, 11
- Fermi level, 12
- Field oxide, 204
- Flat–band condition, 62, 69
- Flat–band voltage, 62, 68, 70
- Flip-chip bonding, 210
- Float-zone technique, 260
- Frenkel defect, 86

- Gate boundary condition, 269
- Gate oxide, 204
- Gatti, 125, 190
- Generation, 70
 - lifetime, 30, 33, 71, 303
 - rate, 316
- Generation/recombination center, 29, 330
- Gettering, 88
- Graded channel approximation, 163, 168, 178, 185
- Guard ring, 107

- Hall, 29
- Hall effect, 19, 20
- Hall mobility, 20
- Hall voltage, 20
- Hole capture, 32, 279, 281
 - cross-section, 286
- Hole emission, 32, 279, 281, 287
- Hybrid pixel detector, 210, 232, 233

- Implantation, 106, 262
- Impurity-gettering, 263
- Indirect semiconductors, 11, 28, 31
- Insulator, 10, 88
- Integrated circuit technology, 195
- Interface state, 69, 308
- Internal gate, 244, 248, 253
- Interstitial, 84, 86, 275–278
- Intrinsic carrier density, 13
- Intrinsic level, 13, 43
- Intrinsic semiconductors, 11, 12
- Inversion, 60, 66, 69
 - layer, 71
 - strong, 67, 166
 - weak, 66, 214, 219
- Inverter, 197, 198

- JFET (Junction Field Effect Transistor), 160, 182, 189, 196, 207
 - current–voltage characteristics, 162

- Kandiah, 185
- Kemmer, 106, 125, 259

- Kinetic energy of electrons, 10
- Kinetic energy of holes, 10
- Knock-on atom, 276

- Landau, 23–25
- Latchup, 205, 206
- Lattice vibration, 276
- Line defect, 86
- Localized energy level, 15, 84
- Lorentzian spectrum, 189
- Low temperature oxide (LTO), 265

- Mass-action law, 16
- Mean free path, 17, 267
- Mean free time, 17
- Mean kinetic energy, 17
- Mean velocity, 17
- Measurement precision
 - energy, 136
 - position, 116, 136
- Metal, 88
- Metal–semiconductor contact, 56–59, 100
- MIS structure, 59
- Mobility, 17
- MOS structure, 59, 117, 118
- MOSFET, 165, 166, 182, 189, 247
- Multiplication coefficient, 54, 55
- Multiplication process, 54
- Multiplication region, 242

- Narrow-gap situation, 269, 270
- Natural oxide, 89
- Neumann boundary condition, 269
- Neutron capture, 275
- NIEL (Non-Ionizing Energy Loss), 277, 288
- NMOS technology, 203
- Noise, 180–199
 - $1/f$, 189, 193, 308
 - in a charge-sensitive amplifier, 191
 - in biasing circuits, 216–222
 - low frequency, 181, 184, 217
 - parallel, 191, 193, 225
 - RTS, 308

- serial, 191, 193
- shot, 181, 182, 191, 217, 218, 308
- switching, 195
- thermal, 180, 182, 308
- white, 193
- Noise correlation, 211, 222, 223
 - serial, 224
- Nonequilibrium operation, 71
- n*-type semiconductors, 14
- Nucleus transmutation, 275

- Occupation probability, 11, 12, 280, 283, 287, 316, 318, 319
- Ohmic contact, 59, 100
- Open loop gain, 198
- Output conductance
 - of an *n*-channel MOSFET, 169
 - of an inverter, 198
- Oxidation, 263
- Oxide charge, 68, 106, 107, 117, 302, 303, 305, 309
- Oxide damage, 302
- Oxi-nitrides, 309

- Pair conversion, 91
- Parseval's theorem, 188
- Passivation, 90, 263, 265
- p*-blocking isolation, 273
- Penetration depth, 92, 96
- Phosphorglass, 265
- Photolithography, 106, 261
- Pinch-off voltage, 161, 162
- Planar technology, 106, 259
- p*-*n* CCD, 137, 138, 144–151, 235, 236
 - device properties, 145
 - experimental applications, 147
 - performance, 147
 - readout, 147
 - working principle, 145
- Point defect, 86, 87, 276, 277
- Poisson equation, 35, 314, 319–321, 323
- Polyimide, 265
- Polysilicon, 88, 139, 204
- Precipitate, 88

- Primary defect, 276–278
- Projective illumination, 261
- Properties
 - of insulators, 89
 - of metals, 90
 - of semiconductors, 80–82
- Proportional mode, 242
- Proximity illumination, 261
- p*-type semiconductor, 14
- Punch-through biasing, 221, 275
- Punch-through mechanism, 213
- Punch-through structure, 212, 213

- Quantum efficiency, 147
- Quasi-Fermi level (QFL), 43, 314, 317, 318, 320, 321

- Radiation length, 82
- Random telegraph signal (RTS), 185, 188
- RCCR filter, 192, 193, 195
- Read, 29
- Readout
 - analog, 111, 117
 - capacitive, 120
 - charge division, 124
 - digital, 112
 - double sided, 116
- Recombination, 28, 70, 93
 - factor, 33
 - lifetime, 30, 157
 - time constant, 33
- Recombination–generation centers, 279
- Rehak, 125
- Reverse annealing, 298, 300, 301
- Reverse bias saturation current, 44
- Richardson constant, 59

- Saturation current
 - of an *n*-channel MOSFET, 169
 - of a *p*-channel MOSFET, 172
- Saturation voltage
 - of an JFET, 162
 - of an *n*-channel MOSFET, 169
 - of a *p*-channel MOSFET, 172
- Scharfetter–Gummel approach, 324

- Shockley, 29
- Shottky barrier, 56, 90
- Sidewards depletion, 125, 137, 234, 243
- Signal cluster, 224
- Silicon nitride (Si_3N_4), 265
- Single photon detection, 241
- Sintering, 106, 265
- Si– SiO_2 interface, 68, 117, 142
- SOI technology, 206, 309
- Source follower, 200
- Space charge region, 41
- Spiking, 264
- Sputtering, 106
- SSJFET (Single-Sided Junction Field Effect Transistor), 234, 236–238
- Stable defect, 276, 277
- Steilheit, 248
- Stress relaxation, 265
- Subthreshold operation, 219
- Surface barrier, 105
- Surface doping, 117
- Surface generated current, 137
- Switched capacitor techniques, 193, 194

- Tetrahedron bond, 8
- Thermal voltage, 159
- Threshold voltage
 - of a *p*-channel MOSFET, 171
 - of an *n*-channel MOSFET, 168
 - of strong inversion, 67
- Transconductance
 - of a bipolar transistor, 159
 - of a DEPFET, 248
 - of a JFET, 162
 - of a *p*-channel MOSFET, 172
 - of a unipolar transistor near threshold, 176
 - of an *n*-channel MOSFET, 169
- Transfer efficiency, 142, 147, 149
- Transistor, 153–179, 182–199
 - bipolar, 153–155, 182, 308
 - junction field effect (JFET), 160, 308
 - MOS, 165, 308
 - *n-p-n*, 153
 - *p-n-p*, 153–155
 - unipolar, 153, 184
- Transition region, 41
- Trapezoidal shaping, 208
- Trapping, 31, 88, 93, 142, 184, 186, 217, 288, 293, 298, 302, 303
- Tunnel effect, 52
- Tunneling, 189, 308
- Type inversion, 289, 303, 304, 330

- Ultrasonic wedge bonding, 230
- Underetching, 262

- Vacancy, 86, 275–277
- Vacancy–interstitial pair, 276
- Valence band, 10
- Velocity saturation, 104

- Weighting function, 195
- Wet etching, 262
- Wide-gap situation, 269, 270
- Work function, 56, 62, 90

- Zener breakdown, 51
- Zener current, 52, 53
- Zinc blende lattice, 7